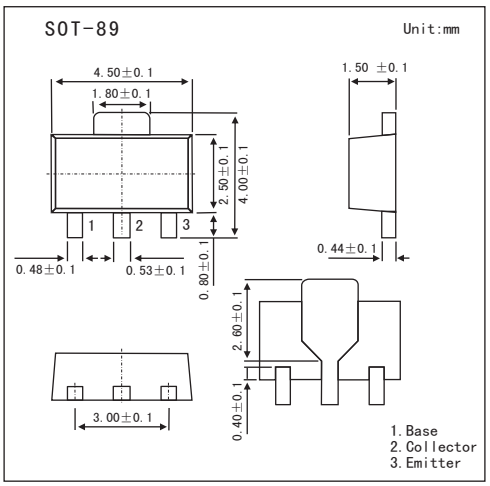
TY Semicondutor®

Product specification

KTD1898



■ Features

- Collector Power Dissipation: P_C=500mW
- Collector Current: I_C=1A

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	100	V
Collector-Emitter voltage	V_{CEO}	80	V
Emitter-base voltage	V_{EBO}	5	V
Collector Current	I_C	1	A
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test conditons	Min	Typ	Max	Unit
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, I_B=0	80			V
Collector Cut-off Current	I_{CBO}	V_{CB}=80V, I_E=0			1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=4V, I_C=0			1	μA
DC Current Gain	h_{FE}	V_{CE}=3V, I_C=500mA	70		400	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA, I_B=20mA			0.4	V
Transition frequency	f_T	V_{CE}=10V, I_C=10mA		100		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V, I_E=0, f=1MHz		20		pF

■ h_{FE} Classification

Marking	ZO	ZR	ZGR
Rank	O	R	GR
h_{FE}	70～140	120～240	200～400